

Green Products

Technical Data Data Sheet N0200, Rev. A

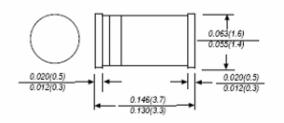
BZV55C/ZMM55C-SERIES

ZENER DIODES

Zener Voltage: 2.4-180V Peak Pulse Power: 500mW

FEATURE

- Low zener impedance
- MINI MELF



Low regulation factor

- + Glass passivated junction
- High temperature soldering guaranteed: 260°C/10S at terminals
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

MECHANICAL DATA

Case: MINI MELF molded glass body Terminals: Plated axial leads, solderable per MIL-STD 750, method 2026 Polarity: Color band denotes cathode end Mounting Position: Any Weight: 0.002 ounce,0.05 gram Marking: Part Name, SSG and Date Code

ORDERING INFORMATION

Device	Package	Shipping
BZV55C/ZMM55C-SERIES	MELF (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

	SYMBOLS	VALUE	UNITS
Zener Current see Table Characteristics			
Power Dissipation at Tamb=25℃(Note 1)	P∞	500	mW
Junction Temperature	Tj	200	°C
Storage Temperature Range	Тыта	-65 to + 200	°C
Thermal resistance junction ambient(Note 1)	R₅⊷	0.3	K/mW
Forward voltage at IF=100mA	Vr	1.0	v

Note 1: Valid provided that leads at a distance of 10mm from case are kept at ambient temperature

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ELECTRICAL CHARACTERISTICS (at TA=25°C unless otherwise noted)

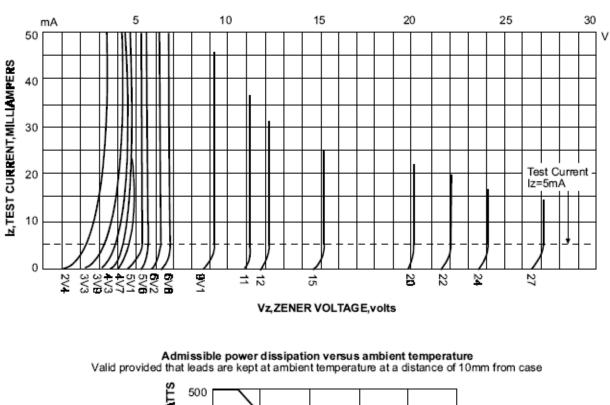
Device Type BZV/ZMM55C2V4 BZV/ZMM55C2V7 BZV/ZMM55C3V0 BZV/ZMM55C3V3 BZV/ZMM55C3V6 BZV/ZMM55C3V9	Min 2.28 2.5 2.8 3.1 3.4	@lzт Мах 2.56 2.9 3.2	Izт mA 5.0 5.0	Zzt@lzt Ohms	Zzk@lzk	lzκ	R	av-		
BZV/ZMM55C2V7 BZV/ZMM55C3V0 BZV/ZMM55C3V3 BZV/ZMM55C3V6 BZV/ZMM55C3V9	2.28 2.5 2.8 3.1 3.4	2.56 2.9 3.2	5.0		Ohren		lr	@Vr	Coefficient	Current Izм
BZV/ZMM55C2V7 BZV/ZMM55C3V0 BZV/ZMM55C3V3 BZV/ZMM55C3V6 BZV/ZMM55C3V9	2.5 2.8 3.1 3.4	2.9 3.2			Ohms	mA	μΑ	Volts	(%/°C)	mA
BZV/ZMM55C3V0 BZV/ZMM55C3V3 BZV/ZMM55C3V6 BZV/ZMM55C3V9	2.8 3.1 3.4	3.2	5.0	85	600	1.0	50	1.0	-0.085	155
BZV/ZMM55C3V3 BZV/ZMM55C3V6 BZV/ZMM55C3V9	3.1 3.4			85	600	1.0	10	1.0	-0.080	135
BZV/ZMM55C3V6 BZV/ZMM55C3V9	3.4		5.0	85	600	1.0	4.0	1.0	-0.075	125
BZV/ZMM55C3V9		3.5	5.0	85	600	1.0	2.0	1.0	-0.070	115
		3.8	5.0	85	600	1.0	2.0	1.0	-0.065	105
B 31 / 31 / 15 5 6 / 6 6	3.7	4.1	5.0	85	600	1.0	2.0	1.0	-0.060	95
BZV/ZMM55C4C3	4.0	4.6	5.0	75	600	1.0	1.0	1.0	±0.055	90
BZV/ZMM55C4V7	4.4	5.0	5.0	60	600	1.0	0.5	1.0	±0.030	85
BZV/ZMM55C5V1	4.8	5.4	5.0	35	550	1.0	0.1	1.0	±0.030	80
BZV/ZMM55C5V6	5.2	6.0	5.0	25	450	1.0	0.1	1.0	+0.038	70
BZV/ZMM55C6V2	5.8	6.6	5.0	10	200	1.0	0.1	2.0	+0.045	64
BZV/ZMM55C6V8	6.4	7.2	5.0	8	150	1.0	0.1	3.0	+0.050	58
BZV/ZMM55C7V5	7.0	7.9	5.0	7	50	1.0	0.1	5.0	+0.058	53
BZV/ZMM55C8V2	7.7	8.7	5.0	7	50	1.0	0.1	6.2	+0.062	74
BZV/ZMM55C9V1	8.5	9.6	5.0	10	50	1.0	0.1	6.8	+0.068	43
BZV/ZMM55C10	9.4	10.6	5.0	15	70	1.0	0.1	7.5	+0.075	40
BZV/ZMM55C11	10.4	11.6	5.0	20	70	1.0	0.1	8.2	+0.076	36
BZV/ZMM55C12	11.4	12.7	5.0	20	90	1.0	0.1	9.1	+0.077	32
BZV/ZMM55C13	12.4	14.1	5.0	26	110	1.0	0.1	10	+0.079	29
BZV/ZMM55C15	13.8	15.6	5.0	30	110	1.0	0.1	11	+0.082	27
BZV/ZMM55C16	15.3	17.1	5.0	40	170	1.0	0.1	12	+0.083	24
BZV/ZMM55C18	16.8	19.1	5.0	50	170	1.0	0.1	13	+0.085	21
BZV/ZMM55C20	18.8	21.2	5.0	55	220	1.0	0.1	15	+0.086	20
BZV/ZMM55C22	20.8	23.3	5.0	55	220	1.0	0.1	16	+0.087	18
BZV/ZMM55C24	22.8	25.6	5.0	80	220	1.0	0.1	18	+0.088	16
BZV/ZMM55C27	25.1	28.9	5.0	80	220	1.0	0.1	20	+0.090	14
BZV/ZMM55C30	28	32	5.0	80	220	1.0	0.1	22	+0.091	13
BZV/ZMM55C33	31	35	5.0	80	220	1.0	0.1	24	+0.092	12
BZV/ZMM55C36	34	38	5.0	80	220	1.0	0.1	27	+0.093	11
BZV/ZMM55C39	37	41	2.5	90	500	0.5	0.1	30	+0.094	10
BZV/ZMM55C43	40	46	2.5	90	600	0.5	0.1	33	+0.095	9.2
BZV/ZMM55C47	44	50	2.5	110	700	0.5	0.1	36	+0.095	8.5
BZV/ZMM55C51	44	54	2.5	125	700	0.5	0.1	39	+0.095	7.8
BZV/ZMM55C56	52	60	2.5	135	1000	0.5	0.1	43	+0.096	7.0
BZV/ZMM55C62	52	66	2.5	150	1000	0.5	0.1	43	+0.096	6.4
BZV/ZMM55C68	64	72	2.5	200	1000	0.5	0.1	51	+0.096	5.9
BZV/ZMM55C75	70	80	2.5	250	1500	0.5	0.1	56	+0.096	5.3
BZV/ZMM55C75 BZV/ZMM55C82	70	80	2.5	300	2000	0.5	0.1	62	+0.096	5.3 4.8
BZV/ZMM55C91	85	96	2.5	450	5000	0.5	0.1	68	+0.096	4.8
									+0.096	
BZV/ZMM55C100 BZV/ZMM55C110	94	106	1.0	450	5000	0.1	0.1	75		4.0
	104	116	1.0	600	5000	0.1	0.1	82	+0.096	3.6
BZV/ZMM55C120	114	127	1.0	800	5000	0.1	0.1	91	+0.096	3.3
BZV/ZMM55C130	124	141	1.0	1000	5000	0.1	0.1	100	+0.096	3.0
BZV/ZMM55C150	138	156	1.0	1200	5000	0.1	0.1	110	+0.096	2.6
BZV/ZMM55C160	153	171	1.0	1500	5000	0.1	0.1	120	+0.096	2.5
BZV/ZMM55C180 BZV/ZMM55C188	168 188	191 212	1.0	1800 2000	5000 5000	0.1	0.1	130 150	+0.096 +0.096	2.2

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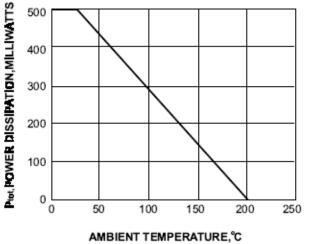


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RATINGS AND CHARACTERISTIC CURVES BZV/ZMM55-SERIES



Breakdown characteristics





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